

# 74LV86

## Quad 2-input exclusive-OR gate

Rev. 03 — 27 November 2007

Product data sheet

### 1. General description

The 74LV86 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC86 and 74HCT86.

The 74LV86 provides a quad 2-input exclusive-OR function.

### 2. Features

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between  $V_{CC} = 2.7$  V and  $V_{CC} = 3.6$  V
- Typical output ground bounce < 0.8 V at  $V_{CC} = 3.3$  V and  $T_{amb} = 25$  °C
- Typical HIGH-level output voltage ( $V_{OH}$ ) undershoot: > 2 V at  $V_{CC} = 3.3$  V and  $T_{amb} = 25$  °C
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

### 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LV86N	-40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74LV86D	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV86DB	-40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LV86PW	-40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV86BQ	-40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

### 4. Functional diagram

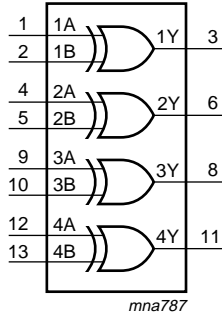


Fig 1. Logic symbol

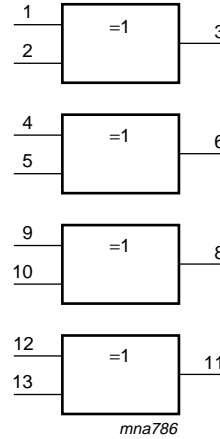


Fig 2. IEC logic symbol

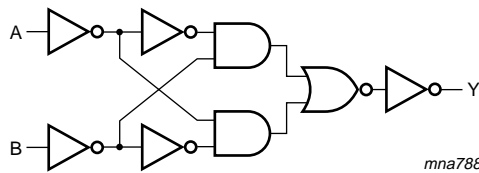


Fig 3. Logic diagram (one gate)

### 5. Pinning information

#### 5.1 Pinning

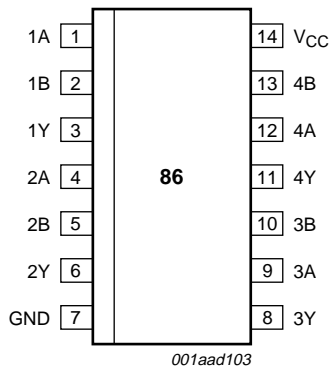
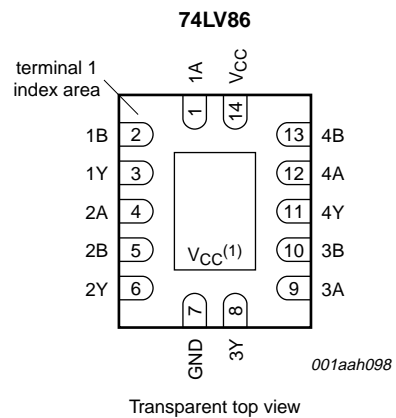


Fig 4. Pin configuration DIP14, SO14 and (T)SSOP14



- (1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.

Fig 5. Pin configuration DHVQFN14

## 5.2 Pin description

**Table 2.** Pin description

Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

**Table 3.** Function table

*H = HIGH voltage level; L = LOW voltage level*

Input		Output
nA	nB	nY
L	L	L
L	H	H
H	L	H
H	H	L

## 7. Limiting values

**Table 4.** Limiting values

*In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).*

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{CC} + 0.5 \text{ V}$	[1] -	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$	[1] -	±50	mA
I <sub>O</sub>	output current	$V_O = -0.5 \text{ V}$ to $(V_{CC} + 0.5 \text{ V})$	-	±25	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C

**Table 4. Limiting values ...continued**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C			
	DIP14 package		[2] -	750	mW
	SO14 package		[3] -	500	mW
	(T)SSOP14 package		[4] -	500	mW
	DHVQFN14 package		[5] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P<sub>tot</sub> derates linearly with 12 mW/K above 70 °C.

[3] P<sub>tot</sub> derates linearly with 8 mW/K above 70 °C.

[4] P<sub>tot</sub> derates linearly with 5.5 mW/K above 60 °C.

[5] P<sub>tot</sub> derates linearly with 4.5 mW/K above 60 °C.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage <sup>[1]</sup>		1.0	3.3	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 1.0 V to 2.0 V	-	-	500	ns/V
		V <sub>CC</sub> = 2.0 V to 2.7 V	-	-	200	ns/V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	100	ns/V
		V <sub>CC</sub> = 3.6 V to 5.5 V	-	-	50	ns/V

[1] The static characteristics are guaranteed from V<sub>CC</sub> = 1.2 V to V<sub>CC</sub> = 5.5 V, but LV devices are guaranteed to function down to V<sub>CC</sub> = 1.0 V (with input levels GND or V<sub>CC</sub>).

## 9. Static characteristics

**Table 6. Static characteristics**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.2 V	0.9	-	-	0.9	-	V
		V <sub>CC</sub> = 2.0 V	1.4	-	-	1.4	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7V <sub>CC</sub>	-	-	0.7V <sub>CC</sub>	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.2 V	-	-	0.3	-	0.3	V
		V <sub>CC</sub> = 2.0 V	-	-	0.6	-	0.6	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.3V <sub>CC</sub>	-	0.3V <sub>CC</sub>	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.2 V	-	1.2	-	-	-	V
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 2.0 V	1.8	2.0	-	1.8	-	V
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 2.7 V	2.5	2.7	-	2.5	-	V
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 3.0 V	2.8	3.0	-	2.8	-	V
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 4.5 V	4.3	4.5	-	4.3	-	V
		I <sub>O</sub> = -6 mA; V <sub>CC</sub> = 3.0 V	2.4	2.82	-	2.2	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 4.5 V	3.6	4.2	-	3.5	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.2 V	-	0	-	-	-	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 2.0 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 2.7 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 3.0 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 4.5 V	-	0	0.2	-	0.2	V
		I <sub>O</sub> = 6 mA; V <sub>CC</sub> = 3.0 V	-	0.25	0.40	-	0.50	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 4.5 V	-	0.35	0.55	-	0.65	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	20.0	-	40	μA
ΔI <sub>CC</sub>	additional supply current	per input; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	500	-	850	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T<sub>amb</sub> = 25 °C.

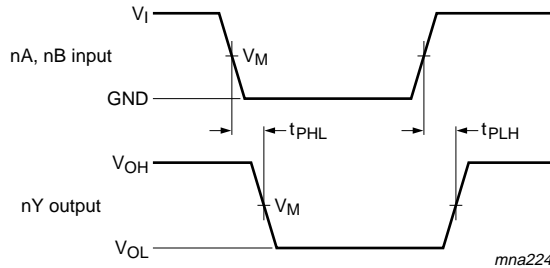
## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**  
*GND = 0 V; For test circuit see Figure 7.*

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA, nB to nY; see Figure 6 <sup>[2]</sup>						
		V <sub>CC</sub> = 1.2 V	-	70	-	-	-	ns
		V <sub>CC</sub> = 2.0 V	-	24	32	-	41	ns
		V <sub>CC</sub> = 2.7 V	-	18	24	-	30	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V; C <sub>L</sub> = 15 pF <sup>[3]</sup>	-	11	-	-	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V <sup>[3]</sup>	-	13	19	-	24	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	16	-	20	ns
C <sub>PD</sub>	power dissipation capacitance	C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>i</sub> = GND to V <sub>CC</sub> <sup>[4]</sup>	-	30	-	-	-	pF

- [1] All typical values are measured at T<sub>amb</sub> = 25 °C.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- [3] Typical values are measured at nominal supply voltage (V<sub>CC</sub> = 3.3 V).
- [4] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz, f<sub>o</sub> = output frequency in MHz  
 C<sub>L</sub> = output load capacitance in pF  
 V<sub>CC</sub> = supply voltage in V  
 N = number of inputs switching  
 Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

## 11. Waveforms



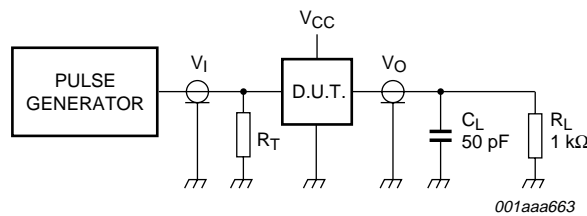
Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 6. The input (nA, nB) to output (nY) propagation delays**

**Table 8. Measurement points**

Supply voltage $V_{CC}$	Input $V_M$	Output $V_M$
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
$\geq 4.5$ V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

**Fig 7. Load circuit for switching times**

**Table 9. Test data**

Supply voltage $V_{CC}$	Input $V_I$	$t_r, t_f$
< 2.7 V	$V_{CC}$	$\leq 2.5$ ns
2.7 V to 3.6 V	2.7 V	$\leq 2.5$ ns
$\geq 4.5$ V	$V_{CC}$	$\leq 2.5$ ns

12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

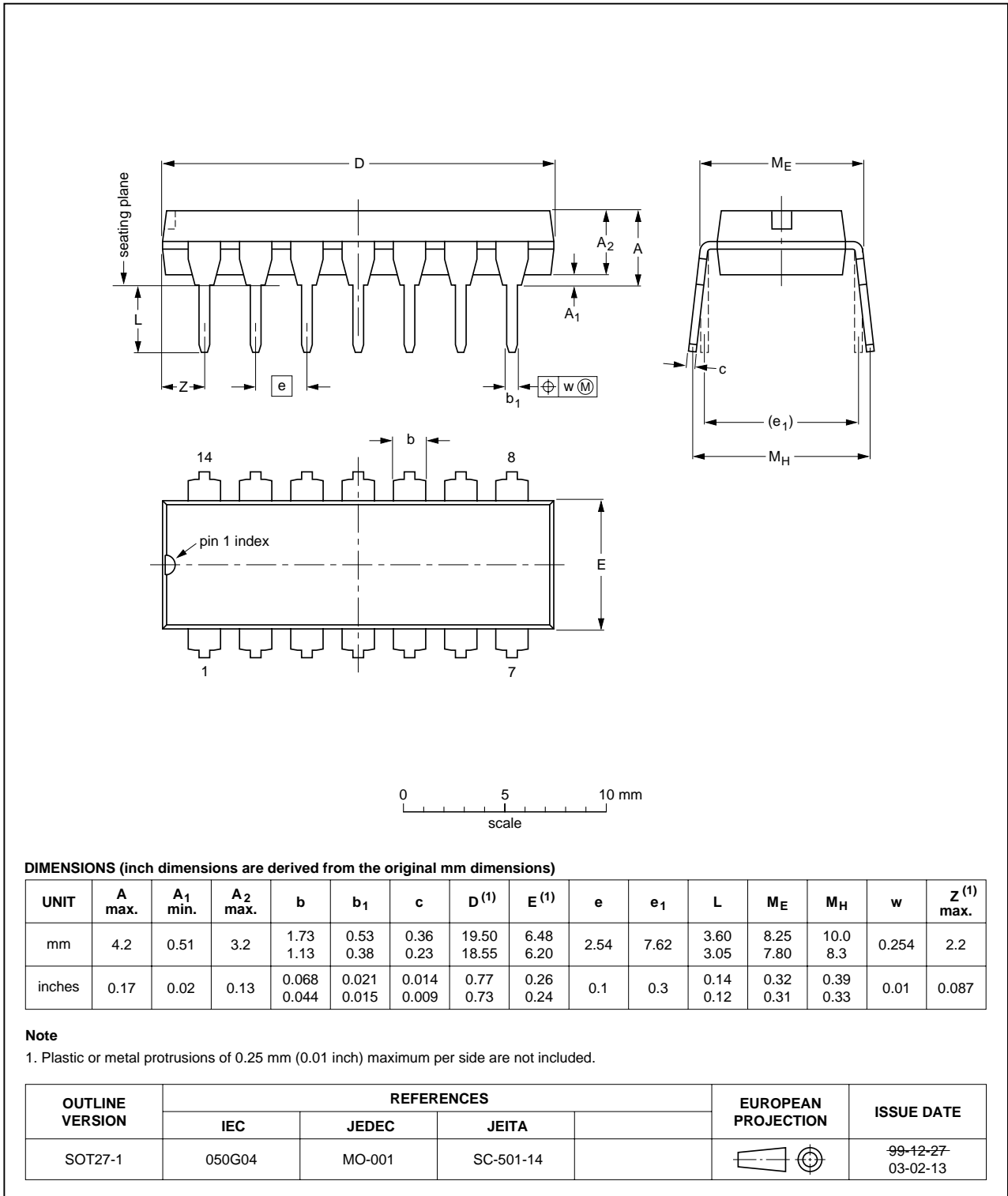


Fig 8. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

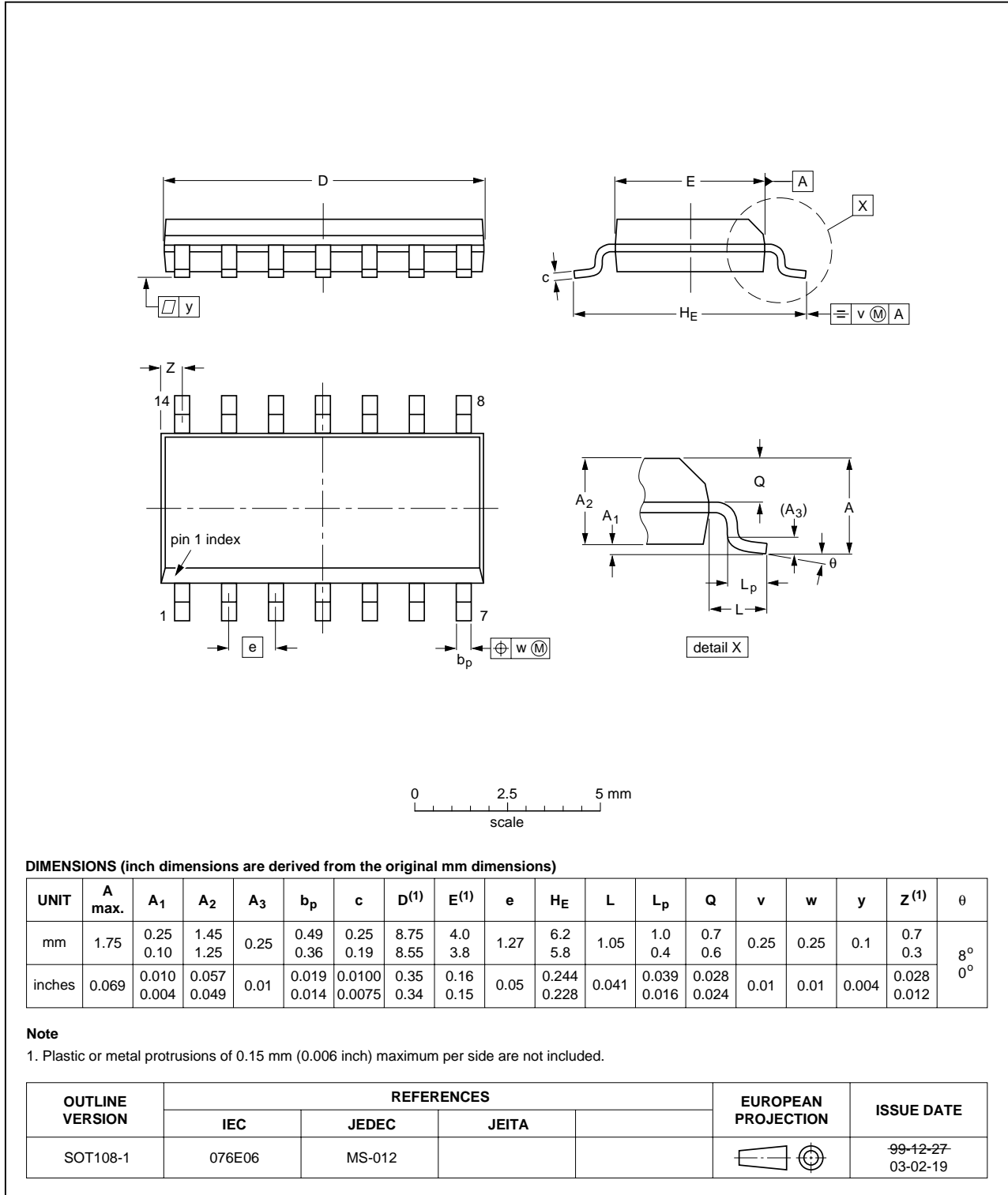


Fig 9. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

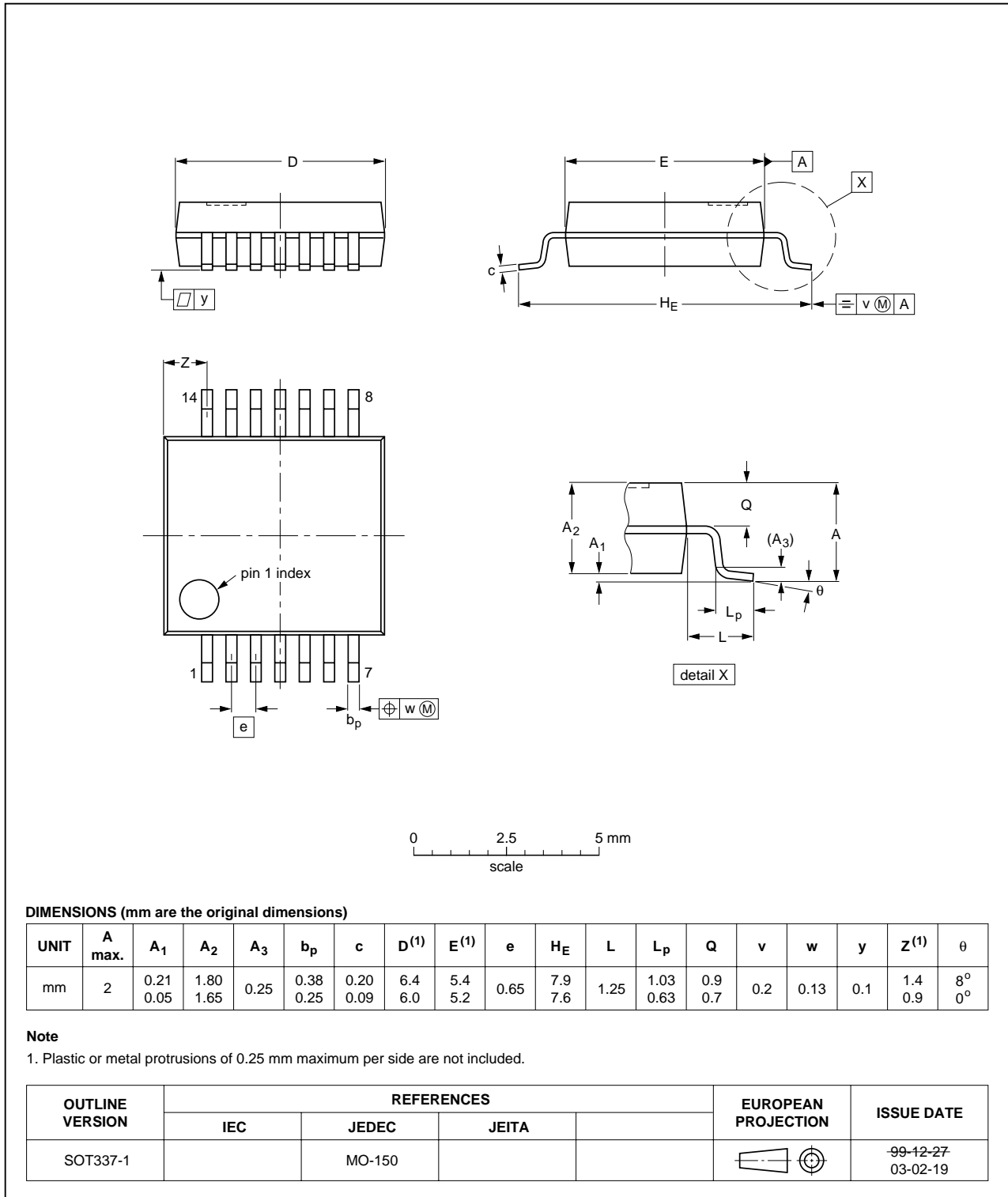


Fig 10. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

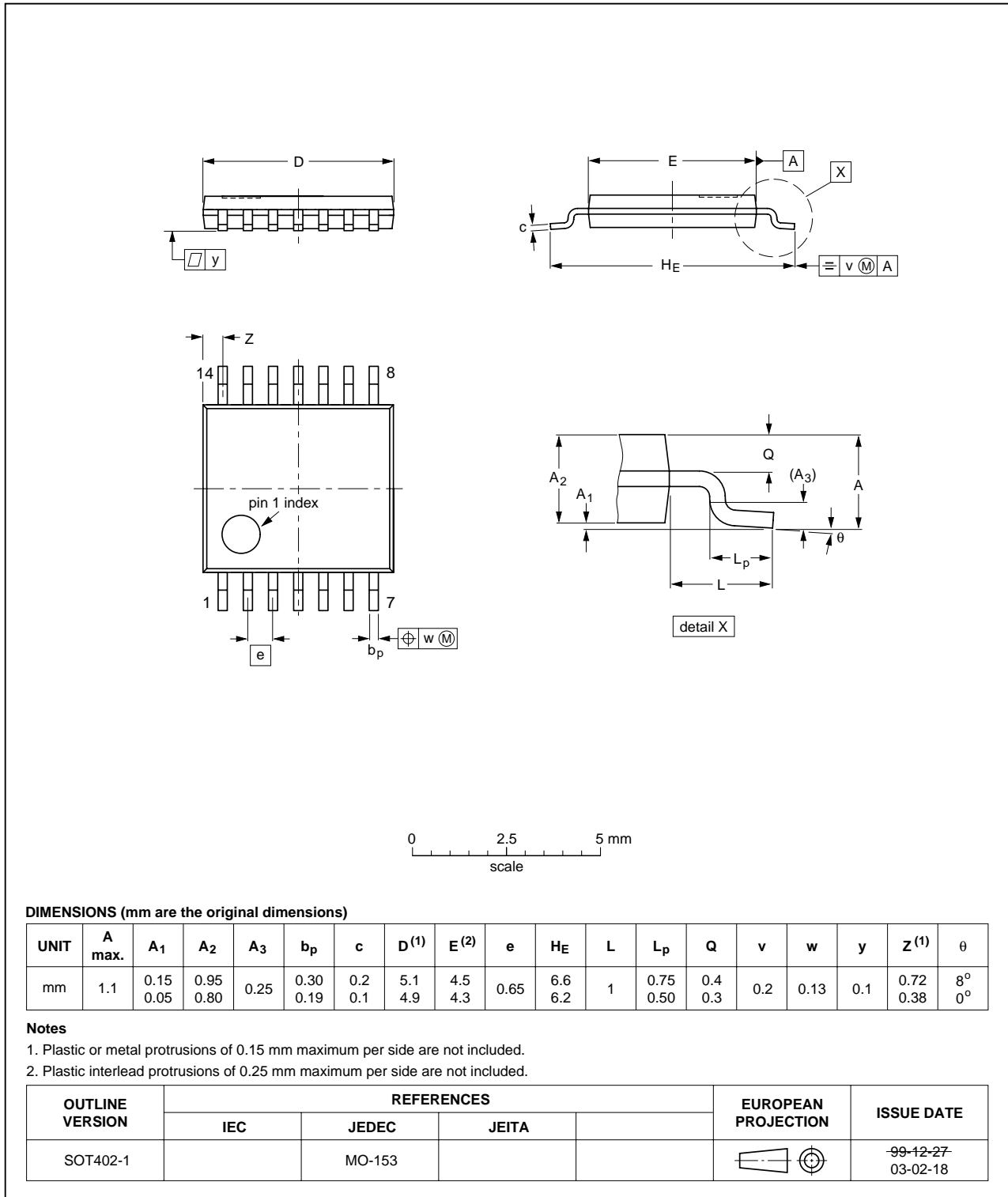


Fig 11. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

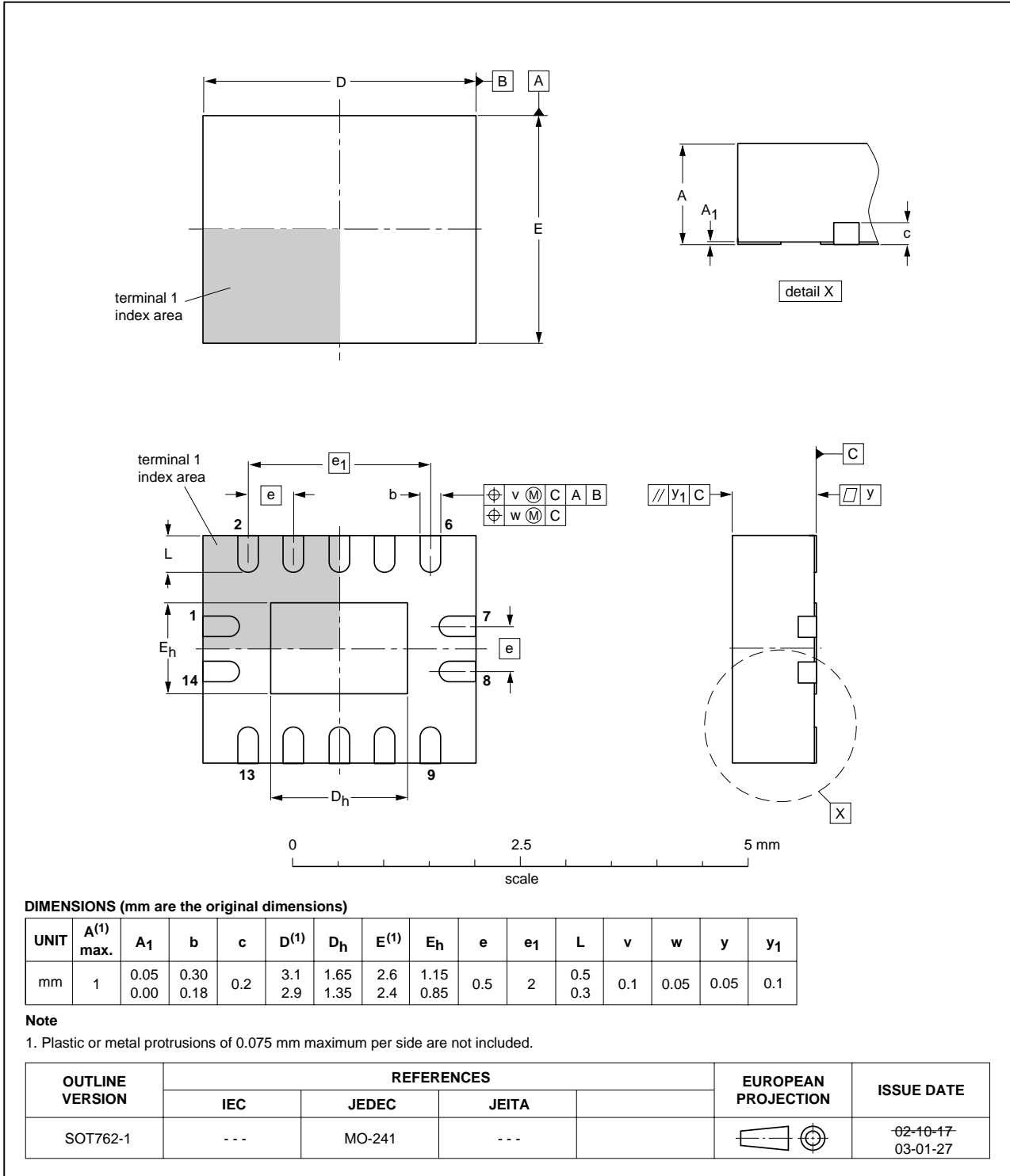


Fig 12. Package outline SOT762-1 (DHVQFN14)

## 13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV86_3	20071127	Product data sheet	-	74LV86_2
Modifications:	<ul style="list-style-type: none"> <li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>• Legal texts have been adapted to the new company name where appropriate.</li> <li>• <a href="#">Section 3</a>: DHVQFN14 package added.</li> <li>• <a href="#">Section 8</a>: derating values added for DHVQFN14 package.</li> <li>• <a href="#">Section 12</a>: outline drawing added for DHVQFN14 package.</li> </ul>			
74LV86_2	19980420	Product specification	-	74LV86_1
74LV86_1	19970203	Product specification	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 17. Contents

<b>1</b>	<b>General description</b> .....	<b>1</b>
<b>2</b>	<b>Features</b> .....	<b>1</b>
<b>3</b>	<b>Ordering information</b> .....	<b>1</b>
<b>4</b>	<b>Functional diagram</b> .....	<b>2</b>
<b>5</b>	<b>Pinning information</b> .....	<b>2</b>
5.1	Pinning .....	2
5.2	Pin description .....	3
<b>6</b>	<b>Functional description</b> .....	<b>3</b>
<b>7</b>	<b>Limiting values</b> .....	<b>3</b>
<b>8</b>	<b>Recommended operating conditions</b> .....	<b>4</b>
<b>9</b>	<b>Static characteristics</b> .....	<b>5</b>
<b>10</b>	<b>Dynamic characteristics</b> .....	<b>6</b>
<b>11</b>	<b>Waveforms</b> .....	<b>7</b>
<b>12</b>	<b>Package outline</b> .....	<b>8</b>
<b>13</b>	<b>Abbreviations</b> .....	<b>13</b>
<b>14</b>	<b>Revision history</b> .....	<b>13</b>
<b>15</b>	<b>Legal information</b> .....	<b>14</b>
15.1	Data sheet status .....	14
15.2	Definitions .....	14
15.3	Disclaimers .....	14
15.4	Trademarks .....	14
<b>16</b>	<b>Contact information</b> .....	<b>14</b>
<b>17</b>	<b>Contents</b> .....	<b>15</b>

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Date of release: 27 November 2007

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